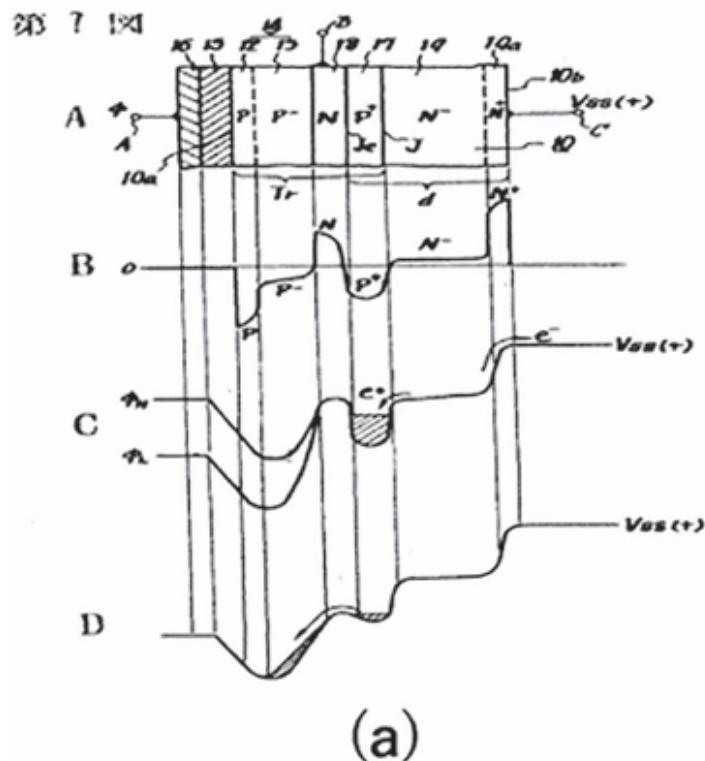


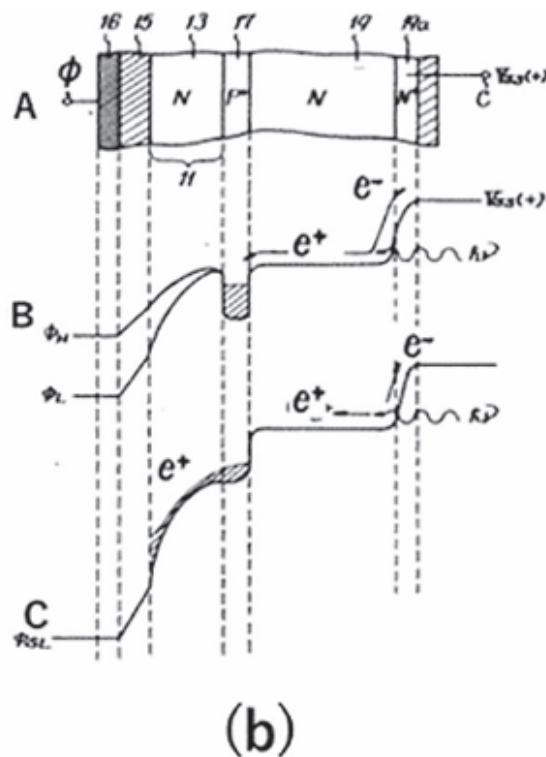
# CHRONOLOGY OF SILICON-BASED IMAGE SENSOR DEVELOPMENT

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JPA1975-127646



JPA1975-127647



JPA1975-134985

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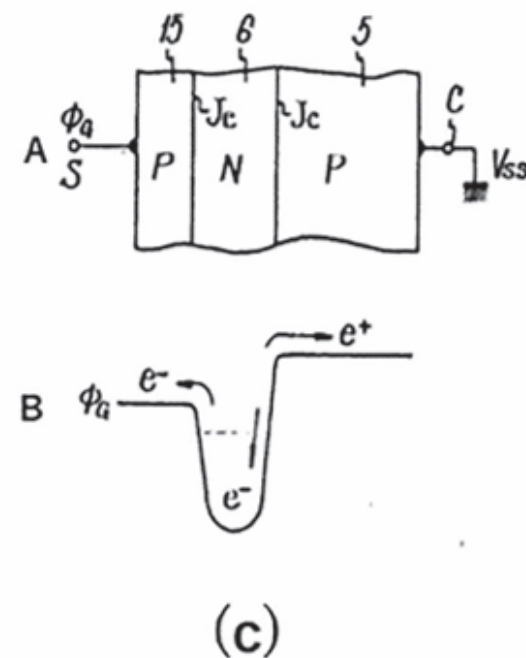


Figure 2: Reproductions from the Japanese Patent Applications of (a) the N+N-P+NP-P triple junction PPD, (b) the N+N-P+N double junction PPD, and (c) the PNP double junction PPD.

3件の出願ともに、Photodiodeの両端がしっかりと金属端子で電圧固定ピン留めされている事を明示しています。